MMBZxxVxL, SZMMBZxxVxL Series

Zener Diodes, 40 Watt Peak Power

SOT-23 Dual Common Cathode Zeners

These dual monolithic silicon zener diodes are designed for applications requiring protection capability. They are intended for use in voltage and ESD sensitive equipment such as computers, printers, business machines, communication systems, medical equipment and other applications. Their dual junction common cathode design protects two separate lines using only one package. These devices are ideal for situations where board space is at a premium.

Specification Features:

- SOT–23 Package Allows Either Two Separate Unidirectional Configurations or a Single Bidirectional Configuration
- Standard Zener Breakdown Voltage Range 15 V, 27 V, 39 V
- Peak Power 40 W @ 1.0 ms (Bidirectional), per Figure 5 Waveform
- ESD Rating of Class 3B (exceeding 16 kV) per the Human Body Model
- ESD Rating of IEC61000-4-2 Level 4, ±30 kV Contact Discharge
- Low Leakage < 100 nA
- Flammability Rating: UL 94 V-O
- SZ Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable
- These are Pb-Free Devices

Mechanical Characteristics:

CASE: Void-free, transfer-molded, thermosetting plastic case

FINISH: Corrosion resistant finish, easily solderable

MAXIMUM CASE TEMPERATURE FOR SOLDERING PURPOSES:

260°C for 10 Seconds

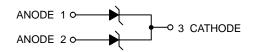


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SOT-23 CASE 318 STYLE 9



MARKING DIAGRAM



XXX = 15D, 27C or 39C M = Date Code

= Pb–Free Package

(Note: Microdot may be in either location)

ORDERING INFORMATION

Device	Package	Shipping [†]
MMBZ15VDLT1G,	SOT-23	3,000 /
SZMMBZ15VDLT1G	(Pb-Free)	Tape & Reel
MMBZ15VDLT3G,	SOT-23	10,000 /
SZMMBZ15VDLT3G	(Pb-Free)	Tape & Reel
MMBZxxVCLT1G,	SOT-23	3,000 /
SZMMBZxxVCLT1G	(Pb-Free)	Tape & Reel
MMBZxxVCLT3G,	SOT-23	10,000 /
SZMMBZxxVCLT3G	(Pb-Free)	Tape & Reel

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

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MAXIMUM RATINGS

Rating	Symbol	Value	Unit
Peak Power Dissipation @ 1.0 ms (Note 1) @ T _L ≤ 25°C	P _{pk}	40	Watts
Total Power Dissipation on FR–5 Board (Note 2) @ T _A = 25°C Derate above 25°C	P _D	225 1.8	mW mW/°C
Thermal Resistance Junction-to-Ambient	$R_{ heta JA}$	556	°C/W
Total Power Dissipation on Alumina Substrate (Note 3) @ T _A = 25°C Derate above 25°C	P _D	300 2.4	mW mW/°C
Thermal Resistance Junction-to-Ambient	$R_{ heta JA}$	417	°C/W
Junction and Storage Temperature Range	T _J , T _{stg}	- 55 to +150	°C
Lead Solder Temperature – Maximum (10 Second Duration)	T _L	260	°C

Stresses exceeding those listed in the Maximum Ratings table may damage the device. If any of these limits are exceeded, device functionality should not be assumed, damage may occur and reliability may be affected.

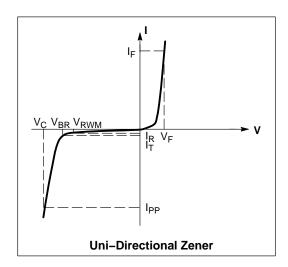
- 1. Nonrepetitive current pulse per Figure 5 and derate above T_A = 25°C per Figure 6.
- 2. $FR-5 = 1.0 \times 0.75 \times 0.62 \text{ in.}$
- 3. Alumina = 0.4 x 0.3 x 0.024 in., 99.5% alumina

ELECTRICAL CHARACTERISTICS

(T_A = 25°C unless otherwise noted)

UNIDIRECTIONAL (Circuit tied to Pins 1 and 3 or 2 and 3)

Symbol	Parameter
I _{PP}	Maximum Reverse Peak Pulse Current
V _C	Clamping Voltage @ I _{PP}
V _{RWM}	Working Peak Reverse Voltage
I _R	Maximum Reverse Leakage Current @ V _{RWM}
V_{BR}	Breakdown Voltage @ I _T
I _T	Test Current
V_{BR}	Maximum Temperature Coefficient of V _{BR}
I _F	Forward Current
V _F	Forward Voltage @ I _F



ELECTRICAL CHARACTERISTICS (T_A = 25°C unless otherwise noted)

UNIDIRECTIONAL (Circuit tied to Pins 1 and 3 or Pins 2 and 3)

 $(V_F = 0.9 \text{ V Max } @ I_F = 10 \text{ mA})$

				Breakdown Voltage			V _C @ I _{PF}	(Note 5)		
	Device	V _{RWM}	I _R @ V _{RWM}	V _{BI}	(Note 4)	(V)	@ ե	v _c	I _{PP}	V_{BR}
Device*	Marking	Volts	nA	Min	Nom	Max	mA	V	Α	mV/°C
MMBZ15VDLT1G/T3G	15D	12.8	100	14.3	15	15.8	1.0	21.2	1.9	12

 $(V_F = 1.1 \text{ V Max } @ I_F = 200 \text{ mA})$

				1	Breakdown Voltage			V _C @ I _{PF}	(Note 5)	
	Device	V _{RWM}	I _R @ V _{RWM}	V _{BI}	(Note 4)	(V)	@ দ	V _C	I _{PP}	V_{BR}
Device*	Marking	Volts	nA	Min	Nom	Max	mA	V	Α	mV/°C
MMBZ27VCLT1G/T3G	27C	22	50	25.65	27	28.35	1.0	38	1.0	26
MMBZ39VCLT1G/T3G	39C	31.2	50	37.05	39	40.95	1.0	55	0.76	35.3

Product parametric performance is indicated in the Electrical Characteristics for the listed test conditions, unless otherwise noted. Product performance may not be indicated by the Electrical Characteristics if operated under different conditions.

^{4.} V_{BR} measured at pulse test current I_T at an ambient temperature of 25°C.

^{5.} Surge current waveform per Figure 5 and derate per Figure 6

^{*}Include SZ-prefix devices where applicable.

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TYPICAL CHARACTERISTICS

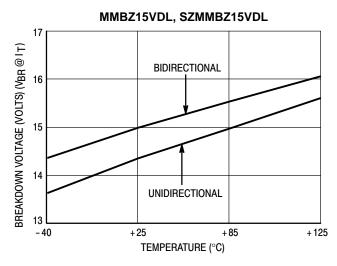


Figure 1. Typical Breakdown Voltage versus Temperature

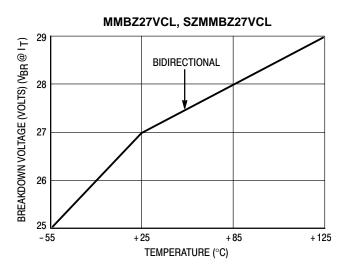


Figure 2. Typical Breakdown Voltage versus Temperature

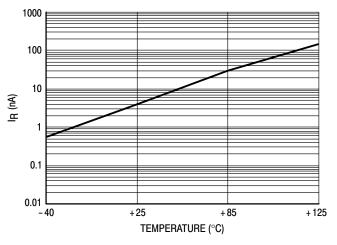


Figure 3. Typical Leakage Current versus Temperature

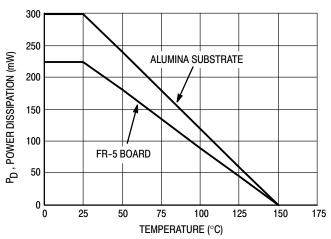


Figure 4. Steady State Power Derating Curve

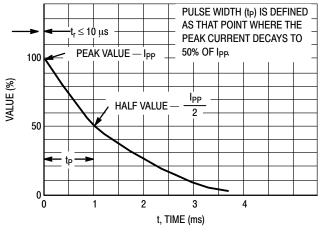


Figure 5. Pulse Waveform

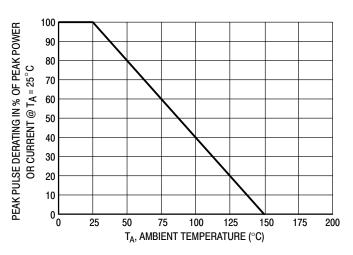


Figure 6. Pulse Derating Curve

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TYPICAL APPLICATIONS

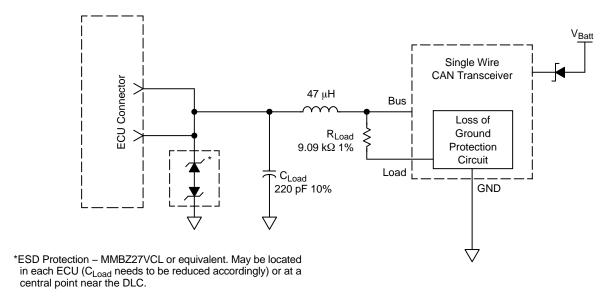


Figure 7. Single Wire CAN Network

Figure is the recommended solution for transient EMI/ESD protection. This circuit is shown in the Society of Automotive Engineers February, 2000 J2411 "Single Wire CAN Network for Vehicle Applications" specification (Figure 6, page 11). Note: the dual common anode zener configuration shown above is electrically equivalent to a dual common cathode zener configuration.

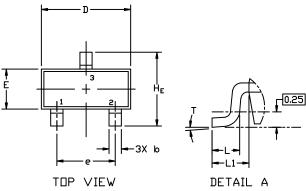




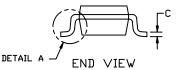
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DATE 01 MAR 2023









NOTES:

- DIMENSIONING AND TOLERANCING PER ASME Y14.5M,1994.
- 2. CONTROLLING DIMENSION: MILLIMETERS
- 3. MAXIMUM LEAD THICKNESS INCLUDES LEAD FINISH. MINIMUM LEAD THICKNESS IS THE MINIMUM THICKNESS OF THE BASE MATERIAL.
- 4. DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH, PROTRUSIONS, OR GATE BURRS.

	MILLIMETERS			INCHES		
DIM	MIN.	N□M.	MAX.	MIN.	N□M.	MAX.
Α	0.89	1.00	1.11	0.035	0.039	0.044
A1	0.01	0.06	0.10	0.000	0.002	0.004
b	0.37	0.44	0.50	0.015	0.017	0.020
С	0.08	0.14	0.20	0.003	0.006	0.008
D	2.80	2.90	3.04	0.110	0.114	0.120
Ε	1.20	1.30	1.40	0.047	0.051	0.055
e	1.78	1.90	2.04	0.070	0.075	0.080
L	0.30	0.43	0.55	0.012	0.017	0.022
L1	0.35	0.54	0.69	0.014	0.021	0.027
HE	2.10	2.40	2.64	0.083	0.094	0.104
Т	0*		10°	0*		10°

GENERIC MARKING DIAGRAM*

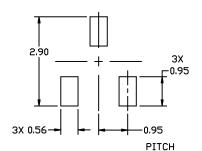


XXX = Specific Device Code

M = Date Code

■ = Pb-Free Package

*This information is generic. Please refer to device data sheet for actual part marking. Pb-Free indicator, "G" or microdot "•", may or may not be present. Some products may not follow the Generic Marking.



RECOMMENDED MOUNTING FOOTPRINT

For additional information on our Pb-Free strategy and soldering details, please download the DN Semiconductor Soldering and Mounting Techniques Reference Manual, SDLDERRM/D.

STYLES ON PAGE 2

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MECHANICAL CASE OUTLINE PACKAGE DIMENSIONS



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DATE 01 MAR 2023

STYLE 1 THRU 5: CANCELLED	STYLE 6: PIN 1. BASE 2. EMITTER 3. COLLECTOR	STYLE 7: PIN 1. EMITTER 2. BASE 3. COLLECTOR	STYLE 8: PIN 1. ANODE 2. NO CONNECTION 3. CATHODE	1	
STYLE 9: PIN 1. ANODE 2. ANODE 3. CATHODE	STYLE 10: PIN 1. DRAIN 2. SOURCE 3. GATE	STYLE 11: PIN 1. ANODE 2. CATHODE 3. CATHODE-ANODE	STYLE 12: PIN 1. CATHODE 2. CATHODE 3. ANODE	STYLE 13: PIN 1. SOURCE 2. DRAIN 3. GATE	STYLE 14: PIN 1. CATHODE 2. GATE 3. ANODE
STYLE 15: PIN 1. GATE 2. CATHODE 3. ANODE	STYLE 16: PIN 1. ANODE 2. CATHODE 3. CATHODE	STYLE 17: PIN 1. NO CONNECTION 2. ANODE 3. CATHODE	STYLE 18: PIN 1. NO CONNECTION 2. CATHODE 3. ANODE	STYLE 19: I PIN 1. CATHODE 2. ANODE 3. CATHODE-ANODE	STYLE 20: PIN 1. CATHODE 2. ANODE 3. GATE
STYLE 21: PIN 1. GATE 2. SOURCE 3. DRAIN	STYLE 22: PIN 1. RETURN 2. OUTPUT 3. INPUT	STYLE 23: PIN 1. ANODE 2. ANODE 3. CATHODE	STYLE 24: PIN 1. GATE 2. DRAIN 3. SOURCE	STYLE 25: PIN 1. ANODE 2. CATHODE 3. GATE	STYLE 26: PIN 1. CATHODE 2. ANODE 3. NO CONNECTION
STYLE 27: PIN 1. CATHODE 2. CATHODE 3. CATHODE	STYLE 28: PIN 1. ANODE 2. ANODE 3. ANODE				

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